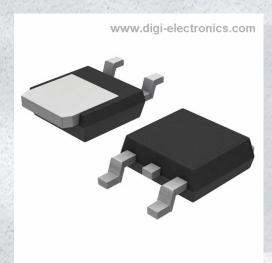


# NID5003NT4 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number NID5003NT4-DG

Manufacturer onsemi

Manufacturer Product Number NID5003NT4

Description IC PWR DRIVER N-CHANNEL 1:1 DPAK

Detailed Description Power Switch/Driver 1:1 N-Channel 20A DPAK



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

| Manufacturer Product Number:                             | Manufacturer:                      |
|--|------------------------------------|
| NID5003NT4   | onsemi                             |
| Series:  | Product Status:                    |
| HDPlus™  | Obsolete                           |
| Switch Type:   | Number of Outputs:                 |
| General Purpose  | 1                                  |
| Ratio - Input:Output:                                    | Output Configuration:              |
| 1:1  | Low Side                           |
| Output Type:   | Interface:                         |
| N-Channel  | On/Off                             |
| Voltage - Load:  | Voltage - Supply (Vcc/Vdd):        |
| 42V (Max)  | Not Required                       |
| Current - Output (Max):                                  | Rds On (Typ):                      |
| 20A  | 42mOhm                             |
| Input Type:  | Features:                          |
| Non-Inverting  | Auto Restart, Slew Rate Controlled |
| Fault Protection:  | Operating Temperature:             |
| Current Limiting (Fixed), Over Temperature, Over Voltage | -55°C ~ 150°C (TJ)                 |
| Mounting Type:   | Supplier Device Package:           |
| Surface Mount  | DPAK                               |
| Package / Case:  | Base Product Number:               |
| TO-252-3, DPAK (2 Leads + Tab), SC-63                    | NID5003                            |

# **Environmental & Export classification**

8541.29.0095

| RoHS Status:       | Moisture Sensitivity Level (MSL): |
|--------------------|-----------------------------------|
| RoHS non-compliant | 1 (Unlimited)                     |
| REACH Status:      | ECCN:                             |
| REACH Unaffected   | EAR99                             |
| HTSUS.             |                                   |

Preferred Device

# Self-Protected FET with Temperature and Current Limit

## 42 V, 20 A, Single N-Channel, DPAK

HDPlus<sup>™</sup> devices are an advanced series of power MOSFETs which utilize ON Semiconductors latest MOSFET technology process to achieve the lowest possible on–resistance per silicon area while incorporating smart features. Integrated thermal and current limits work together to provide short circuit protection. The devices feature an integrated Drain–to–Gate Clamp that enables them to withstand high energy in the avalanche mode. The Clamp also provides additional safety margin against unexpected voltage transients. Electrostatic Discharge (ESD) protection is provided by an integrated Gate–to–Source Clamp.

#### **Features**

- Short Circuit Protection/Current Limit
- Thermal Shutdown with Automatic Restart
- I<sub>DSS</sub> Specified at Elevated Temperature
- Avalanche Energy Specified
- Slew Rate Control for Low Noise Switching
- Overvoltage Clamped Protection

#### MOSFET MAXIMUM RATINGS (T<sub>.I</sub> = 25°C unless otherwise noted)

| Rating  | Symbol   | Value           | Unit   |
|---|--|-----------------|--------|
| Drain-to-Source Voltage Internally Clamped  | $V_{DSS}$  | 42              | Vdc    |
| Gate-to-Source Voltage  | $V_{GS}$   | ±14             | Vdc    |
| Drain Current Continuous  | I <sub>D</sub>   | Internally L    | imited |
| Total Power Dissipation  @ T <sub>A</sub> = 25°C (Note 1)  @ T <sub>A</sub> = 25°C (Note 2)   | P <sub>D</sub>   | 1.3<br>2.3      | W      |
| Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)   | $egin{array}{l} R_{	hetaJC} \ R_{	hetaJA} \ R_{	hetaJA} \end{array}$ | 3.0<br>95<br>54 | °C/W   |
| Single Pulse Drain-to-Source Avalanche Energy $(V_{DD}=25~\text{Vdc},~V_{GS}=5.0~\text{Vdc},\\ I_L=3.2~\text{Apk},~L=120~\text{mH},~R_G=25~\Omega)$ | E <sub>AS</sub>  | 600             | mJ     |
| Operating and Storage Temperature Range (Note 3)  | T <sub>J</sub> , T <sub>stg</sub>                                    | –55 to<br>150   | °C     |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

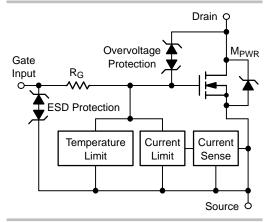
- 1. Surface mounted onto minimum pad size (0.412" square) FR4 PCB, 1 oz cu.
- 2. Mounted onto 1" square pad size (1.127" square) FR4 PCB, 1 oz cu.
- 3. Normal pre-fault operating range. See thermal limit range conditions.

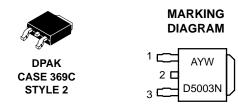


#### ON Semiconductor®

#### http://onsemi.com

| V <sub>DSS</sub><br>(Clamped) | R <sub>DS(on)</sub> TYP | I <sub>D</sub> MAX<br>(Limited) |
|-------------------------------|-------------------------|---------------------------------|
| 42 V                          | 42 mΩ @ 10 V            | 20 A*                           |





 D5003N = Device Code
 1 = Gate

 A = Assembly Location
 2 = Drain

 Y = Year
 3 = Source

 W = Work Week

#### ORDERING INFORMATION

| Device     | Package | Shipping <sup>†</sup> |
|------------|---------|-----------------------|
| NID5003NT4 | DPAK    | 2500/Tape & Reel      |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

\*Max current may be limited below this value depending on input conditions.

#### **MOSFET ELECTRICAL CHARACTERISTICS** ( $T_J = 25$ °C unless otherwise noted)

| С   | Symbol   | Min                                 | Тур         | Max        | Unit     |               |
|---|--|-------------------------------------|-------------|------------|----------|---------------|
| OFF CHARACTERISTICS   |  |                                     |             |            |          |               |
| Drain-to-Source Clamped Br $(V_{GS} = 0 \text{ Vdc}, I_D = 250 \mu\text{Ad})$ $(V_{GS} = 0 \text{ Vdc}, I_D = 250 \mu\text{Ad})$              | V <sub>(BR)DSS</sub>   | 42<br>40                            | 46<br>45    | 51<br>51   | Vdc      |               |
| Zero Gate Voltage Drain Curro<br>( $V_{DS} = 32 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}$<br>( $V_{DS} = 32 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}$   | c)   | I <sub>DSS</sub>                    | -<br>-      | 0.6<br>2.5 | 5.0<br>- | μAdc          |
| Gate Input Current<br>(V <sub>GS</sub> = 5.0 Vdc, V <sub>DS</sub> = 0 Vd  | lc)  | I <sub>GSSF</sub>                   | -           | 50         | 125      | μAdc          |
| ON CHARACTERISTICS  |  |                                     |             | 1          |          |               |
| Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.2 \text{ mAdc})$<br>Threshold Temperature Coefficients                                      |  | V <sub>GS(th)</sub>                 | 1.0         | 1.7<br>5.0 | 2.2      | Vdc<br>-mV/°C |
| Static Drain-to-Source On-R<br>( $V_{GS} = 10 \text{ Vdc}$ , $I_D = 3.0 \text{ Add}$<br>( $V_{GS} = 10 \text{ Vdc}$ , $I_D = 3.0 \text{ Add}$ | R <sub>DS(on)</sub>  | -<br>-                              | 42<br>76    | 51<br>104  | mΩ       |               |
| Static Drain-to-Source On-R<br>( $V_{GS} = 5.0 \text{ Vdc}$ , $I_D = 3.0 \text{ Ad}$<br>( $V_{GS} = 5.0 \text{ Vdc}$ , $I_D = 3.0 \text{ Ad}$ | R <sub>DS(on)</sub>  | -<br>-                              | 50<br>88    | 58<br>125  | mΩ       |               |
| Source-Drain Forward On Vo<br>(I <sub>S</sub> = 7.0 A, V <sub>GS</sub> = 0 V)   | V <sub>SD</sub>  | -                                   | 0.95        | 1.1        | V        |               |
| SWITCHING CHARACTERIST  | rics   |                                     |             | •          | •        | •             |
| Turn-on Time<br>(V <sub>in</sub> to 90% I <sub>D</sub> )  | $R_L = 4.7 \Omega$ , $V_{in} = 0$ to 10 V, $V_{DD} = 12 V$   | T <sub>(on)</sub>                   | -           | 16         | 20       | μs            |
| Turn-off Time<br>(V <sub>in</sub> to 10% I <sub>D</sub> )   | $R_L = 4.7 \ \Omega, \ V_{in} = 0 \text{ to } 10 \ V, \ V_{DD} = 12 \ V$                                       | T <sub>(off)</sub>                  | _           | 80         | 100      |               |
| Slew Rate On  | $R_L = 4.7 \ \Omega$ , $V_{in} = 0$ to 10 V, $V_{DD} = 12 \ V$   | -dV <sub>DS</sub> /dt <sub>on</sub> | -           | 1.4        | _        | V/µs          |
| Slew Rate Off   | $R_L = 4.7 \ \Omega, \ V_{in} = 10 \ to \ 0 \ V, \ V_{DD} = 12 \ V$  | dV <sub>DS</sub> /dt <sub>off</sub> | -           | 0.5        | -        | V/μs          |
| SELF PROTECTION CHARAC  | TERISTICS (T <sub>J</sub> = 25°C unless otherwise no   | oted) (Note 5)                      |             |            |          |               |
| Current Limit   | $(V_{GS} = 5.0 \text{ Vdc})$<br>$V_{DS} = 10 \text{ V } (V_{GS} = 5.0 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ | I <sub>LIM</sub>                    | 12<br>7     | 18<br>13   | 24<br>18 | Adc           |
| Current Limit   | (V <sub>GS</sub> = 10 Vdc)<br>V <sub>DS</sub> = 10 V (V <sub>GS</sub> = 10 Vdc, T <sub>J</sub> = 150°C)        | I <sub>LIM</sub>                    | 18<br>13    | 22<br>18   | 30<br>25 |               |
| Temperature Limit (Turn-off)  | V <sub>GS</sub> = 5.0 Vdc  | T <sub>LIM(off)</sub>               | 150         | 175        | 200      | °C            |
| Thermal Hysteresis  | Thermal Hysteresis V <sub>GS</sub> = 5.0 Vdc   |                                     | -           | 15         | _        | °C            |
| Temperature Limit (Turn-off)  | Temperature Limit (Turn-off) V <sub>GS</sub> = 10 Vdc  |                                     | 150         | 165        | 185      | °C            |
| Thermal Hysteresis  | V <sub>GS</sub> = 10 Vdc   | $\Delta T_{LIM(on)}$                | _           | 15         | _        | °C            |
| Input Current during<br>Thermal Fault   | $V_{DS} = 35 \text{ V}, (V_{GS} = 5.0 \text{ V}, T_j = 150^{\circ}\text{C})$                                   |                                     | 0.6         | _          | -        | mA            |
| Input Current during $V_{DS} = 35 \text{ V}, (V_{GS} = 10 \text{ V}, T_j = 150^{\circ}\text{C})$ Thermal Fault                                |  | I <sub>g(fault)</sub>               | 2.0         | _          | -        | mA            |
| ESD ELECTRICAL CHARACT  | ERISTICS (T <sub>J</sub> = 25°C unless otherwise not   | ed)                                 |             |            |          |               |
| Electro–Static Discharge Capability Human Body Model (HBM) Machine Model (MM)   |  | ESD                                 | 4000<br>400 |            |          | V             |

<sup>4.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Fault conditions are viewed as beyond the normal operating range of the part.

#### **TYPICAL PERFORMANCE CURVES**

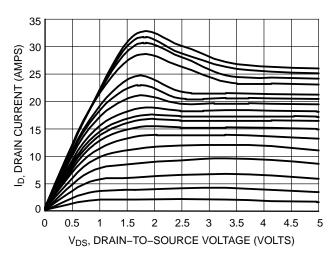
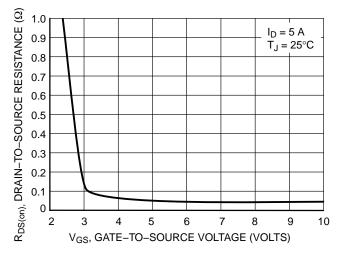


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



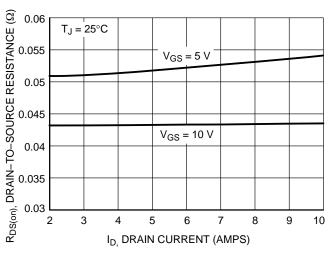
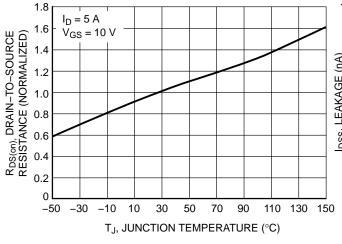


Figure 3. On–Resistance vs. Gate–to–Source Voltage

Figure 4. On–Resistance vs. Drain Current and Gate Voltage



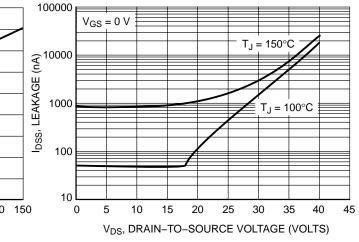


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

### **TYPICAL PERFORMANCE CURVES**

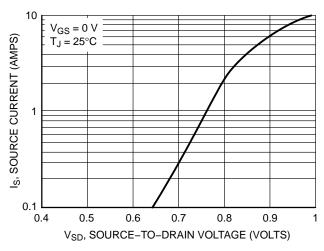
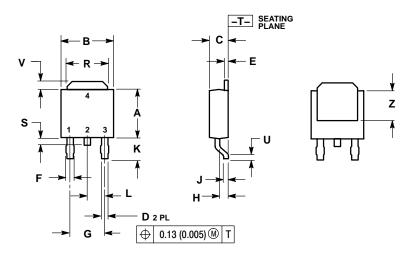


Figure 7. Diode Forward Voltage vs. Current

#### **PACKAGE DIMENSIONS**

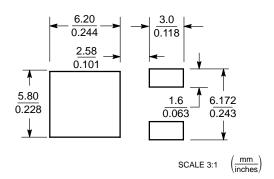
**DPAK** CASE 369C-01 ISSUE O



|     | INCHES |       | MILLIN   | IETERS |  |
|-----|--------|-------|----------|--------|--|
| DIM | MIN    | MAX   | MIN      | MAX    |  |
| Α   | 0.235  | 0.245 | 5.97     | 6.22   |  |
| В   | 0.250  | 0.265 | 6.35     | 6.73   |  |
| С   | 0.086  | 0.094 | 2.19     | 2.38   |  |
| D   | 0.027  | 0.035 | 0.69     | 0.88   |  |
| Е   | 0.018  | 0.023 | 0.46     | 0.58   |  |
| F   | 0.037  | 0.045 | 0.94     | 1.14   |  |
| G   | 0.180  | BSC   | 4.58 BSC |        |  |
| Н   | 0.034  | 0.040 | 0.87     | 1.01   |  |
| J   | 0.018  | 0.023 | 0.46     | 0.58   |  |
| K   | 0.102  | 0.114 | 2.60     | 2.89   |  |
| L   | 0.090  | BSC   | 2.29     | BSC    |  |
| R   | 0.180  | 0.215 | 4.57     | 5.45   |  |
| S   | 0.025  | 0.040 | 0.63     | 1.01   |  |
| U   | 0.020  |       | 0.51     |        |  |
| ٧   | 0.035  | 0.050 | 0.89     | 1.27   |  |
| Z   | 0.155  |       | 3.93     |        |  |

- STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

#### **SOLDERING FOOTPRINT**



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